NSN 5961-01-007-5585

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-007-5585 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** 0.225 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Component Name And Quantity:** 2 transistor **Mounting Method:** Unthreaded hole **Features Provided:** Burn in and gold plated leads **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: -80.0 breakdown voltage, collector-to-base, emitter open all transistor and -80.0 breakdown voltage, collector-to-emitter, with specified resistance between base and emitter all transistor and 8.0 breakdown voltage, emitter-to-base, collector open all transistor **Current Rating Per Characteristic:** 10.00 amperes source cutoff current all transistor **Power Rating Per Characteristic:** 50.0 watts small-signal input power, common-collector preset all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius case and 175.0 degrees celsius junction **Precious Material And Location:** Leads gold **Precious Material: Terminal Type And Quantity:** 8 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:** No

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